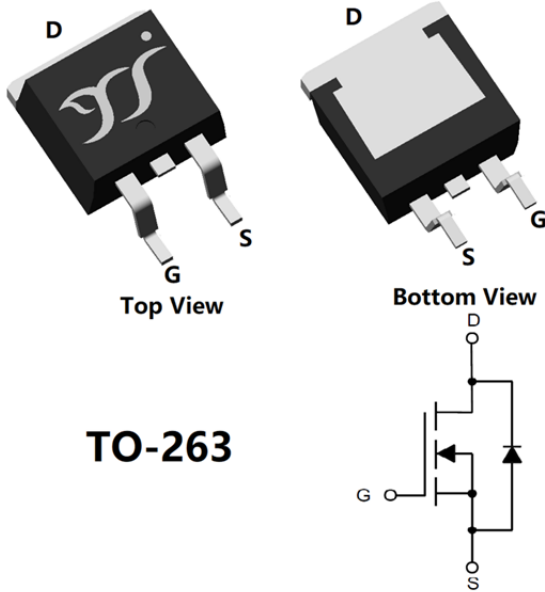


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 40V
- I_D 155A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <2.5mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Uninterruptible power supply
- DC-DC converter

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	40	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ C$	I_D	28	A
	$T_A=100^\circ C$		20	
	$T_C=25^\circ C$		155	
	$T_C=100^\circ C$		109	
Pulsed Drain Current ^A		I_{DM}	465	A
Avalanche energy ^B		EAS	676	mJ
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	5	W
	$T_A=100^\circ C$		2.5	
	$T_C=25^\circ C$		150	
	$T_C=100^\circ C$		75	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+175	$^\circ C$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	25	30	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.8	1	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB155G04H	F2	YJB155G04H	800	/	8000	13" reel



YJB155G04H

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
		V _{DS} =40V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	2	3	4	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	1.9	2.5	mΩ
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	-	1.2	V
Gate resistance	R _G	f=1MHz	-	1.0	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	155	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, f=1MHz	-	4380	-	pF
Output Capacitance	C _{oss}		-	1490	-	
Reverse Transfer Capacitance	C _{rss}		-	30	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =20V, I _D =55A	-	56.56	-	nC
Gate-Source Charge	Q _{gs}		-	27	-	
Gate-Drain Charge	Q _{gd}		-	5.66	-	
Reverse Recovery Charge	Q _{rr}	I _F =55A, di/dt=100A/us	-	52.58	-	nC
Reverse Recovery Time	t _{rr}		-	58.2	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =20V, I _D =55A R _{GEN} =3Ω	-	21.8	-	ns
Turn-on Rise Time	t _r		-	8.6	-	
Turn-off Delay Time	t _{D(off)}		-	43.8	-	
Turn-off fall Time	t _f		-	51.7	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_G=10V, R_G=25Ω, L=2mH, I_{AS}=26A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design.



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Typical Electrical and Thermal Characteristics Diagrams

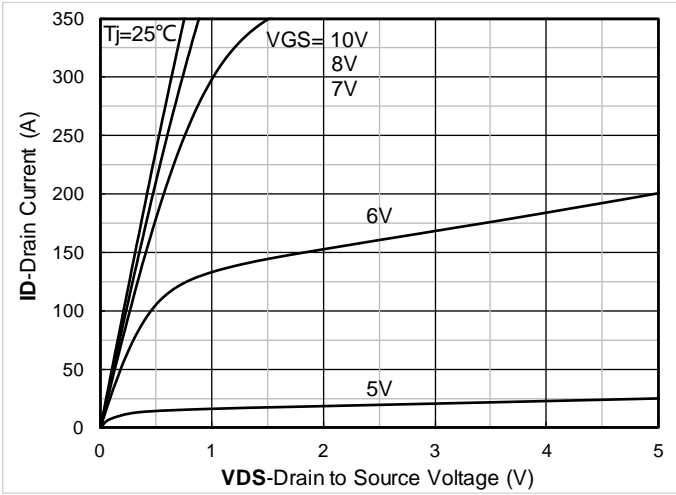


Figure1. Output Characteristics

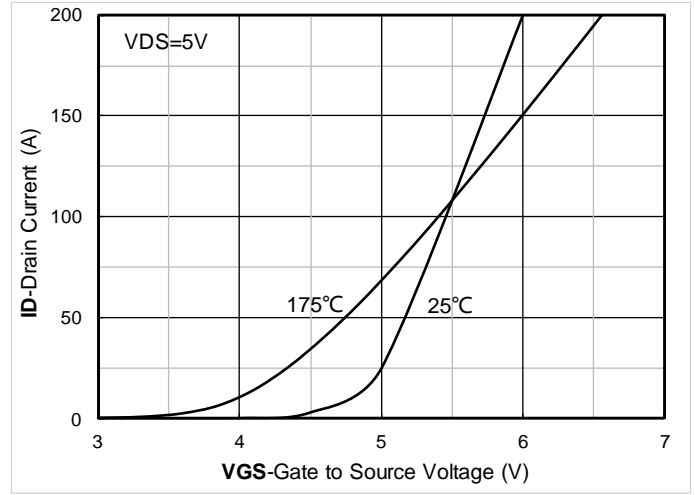


Figure2. Transfer Characteristics

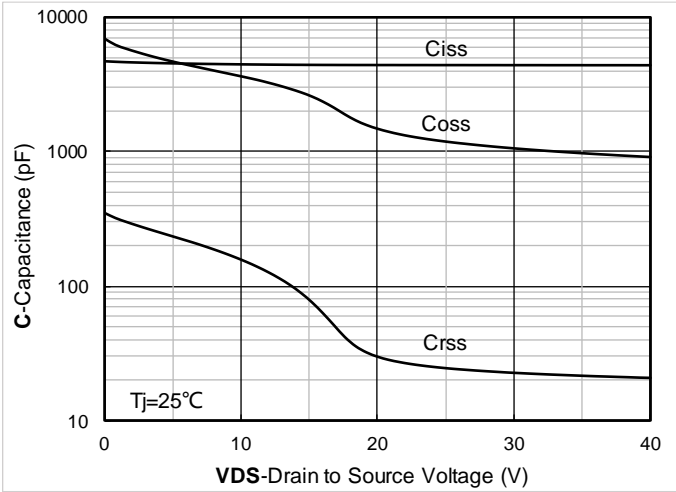


Figure3. Capacitance Characteristics

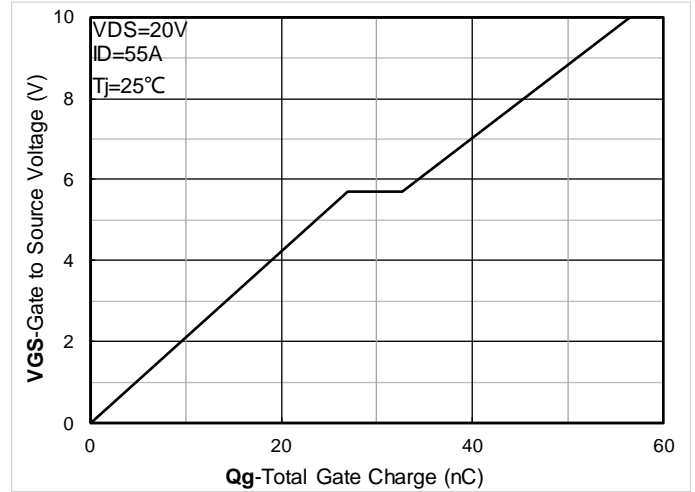


Figure4. Gate Charge

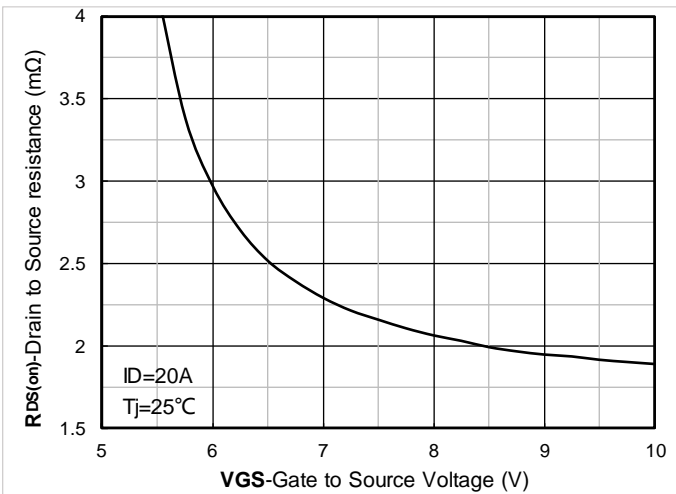


Figure5. On-Resistance vs Gate to Source Voltage

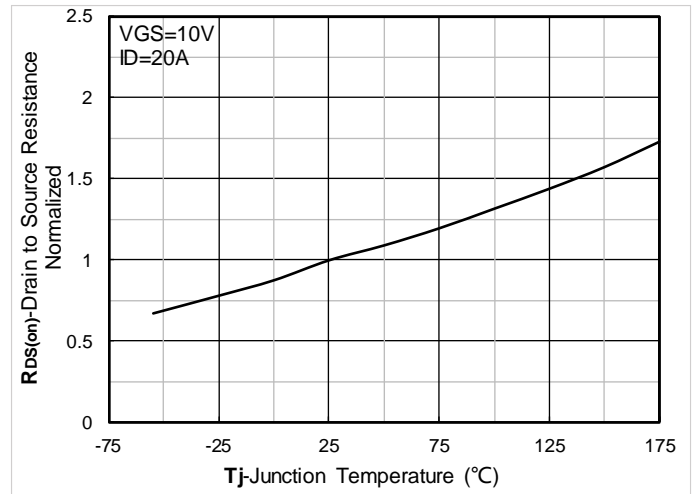


Figure6. Normalized On-Resistance



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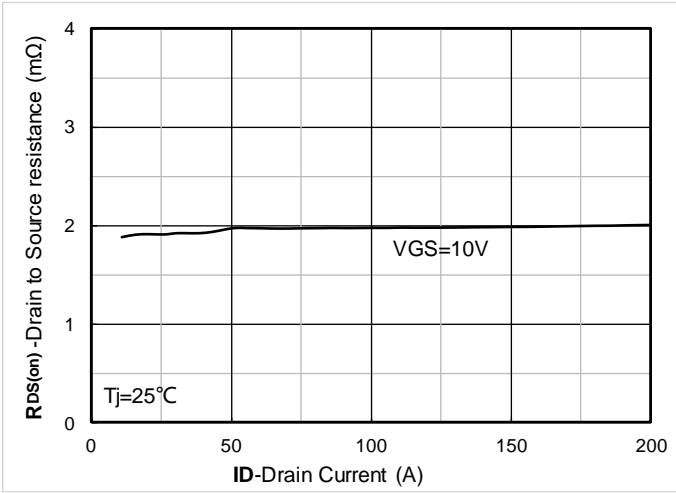


Figure7. RDS(on) VS Drain Current

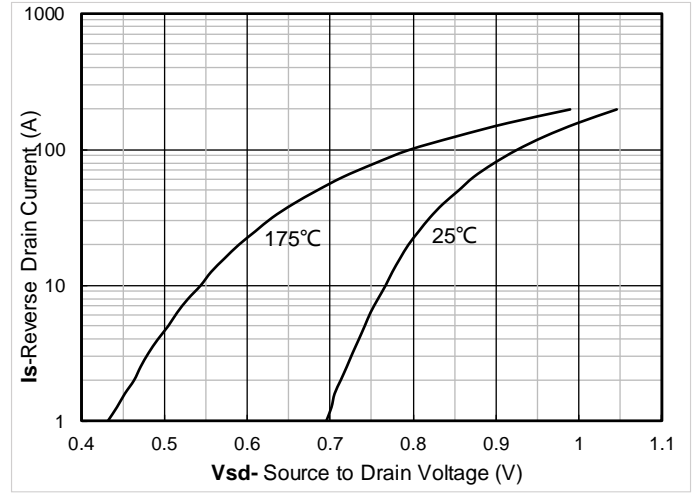


Figure8. Forward characteristics of reverse diode

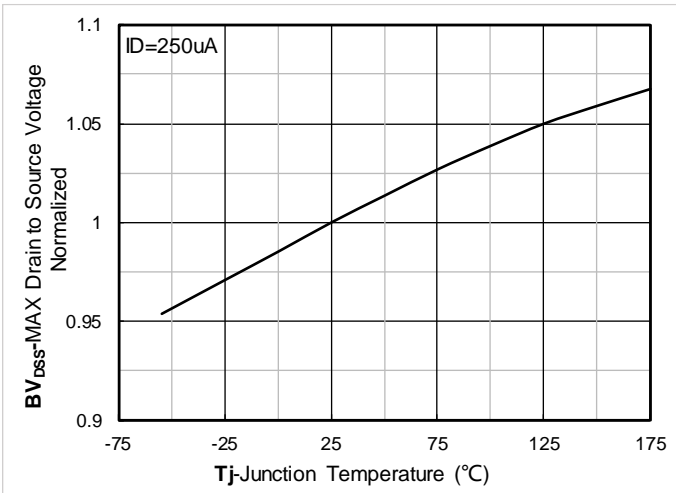


Figure9. Normalized breakdown voltage

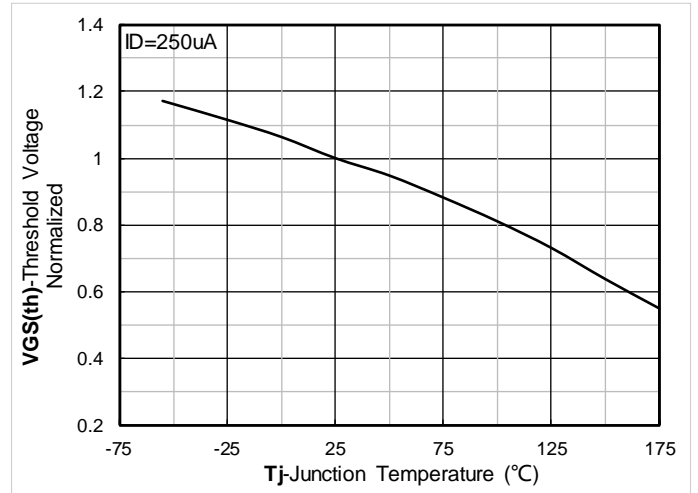


Figure10. Normalized Threshold voltage

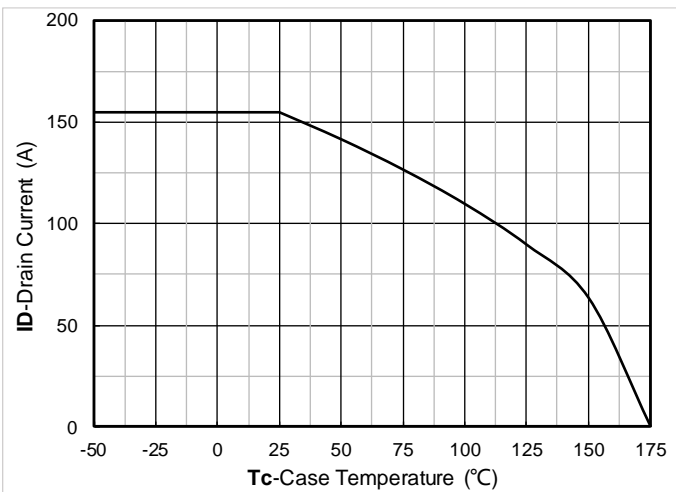


Figure11. Current dissipation

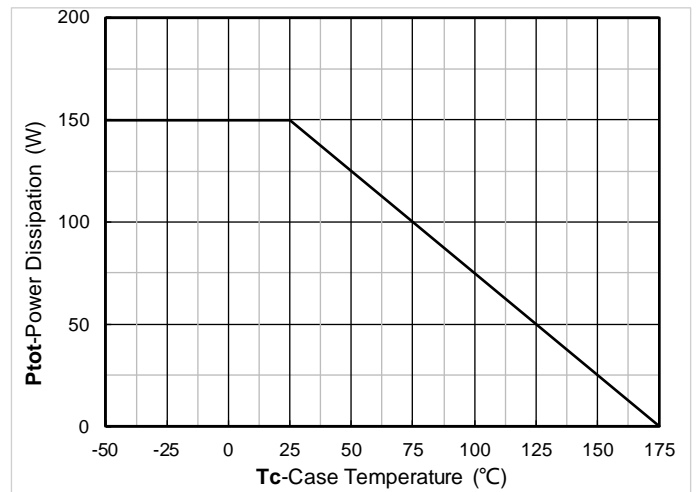


Figure12. Power dissipation



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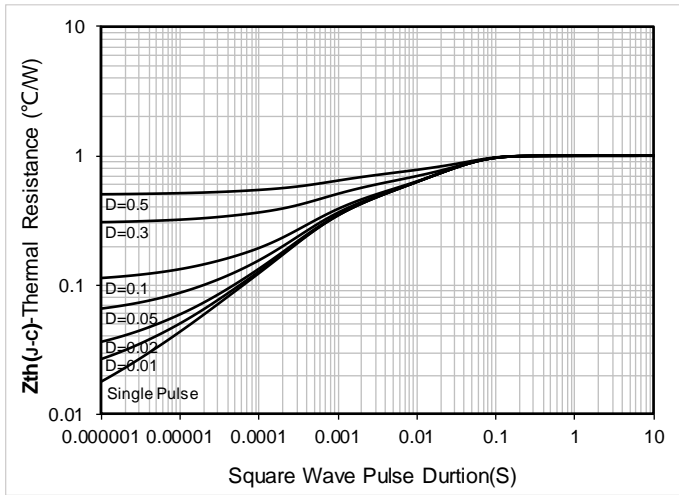


Figure13. Maximum Transient Thermal Impedance

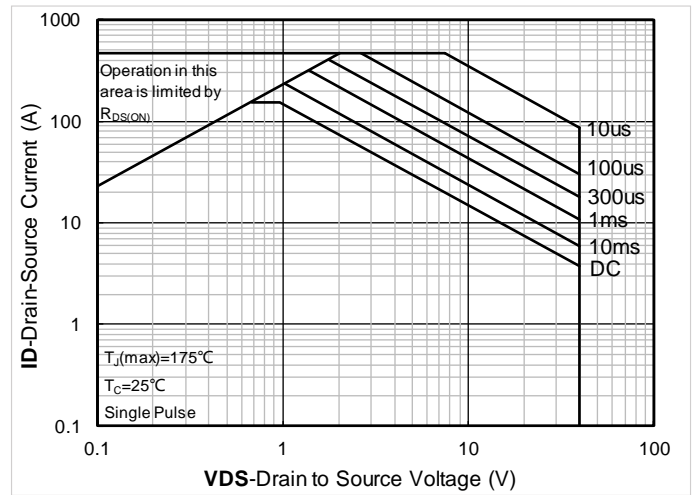
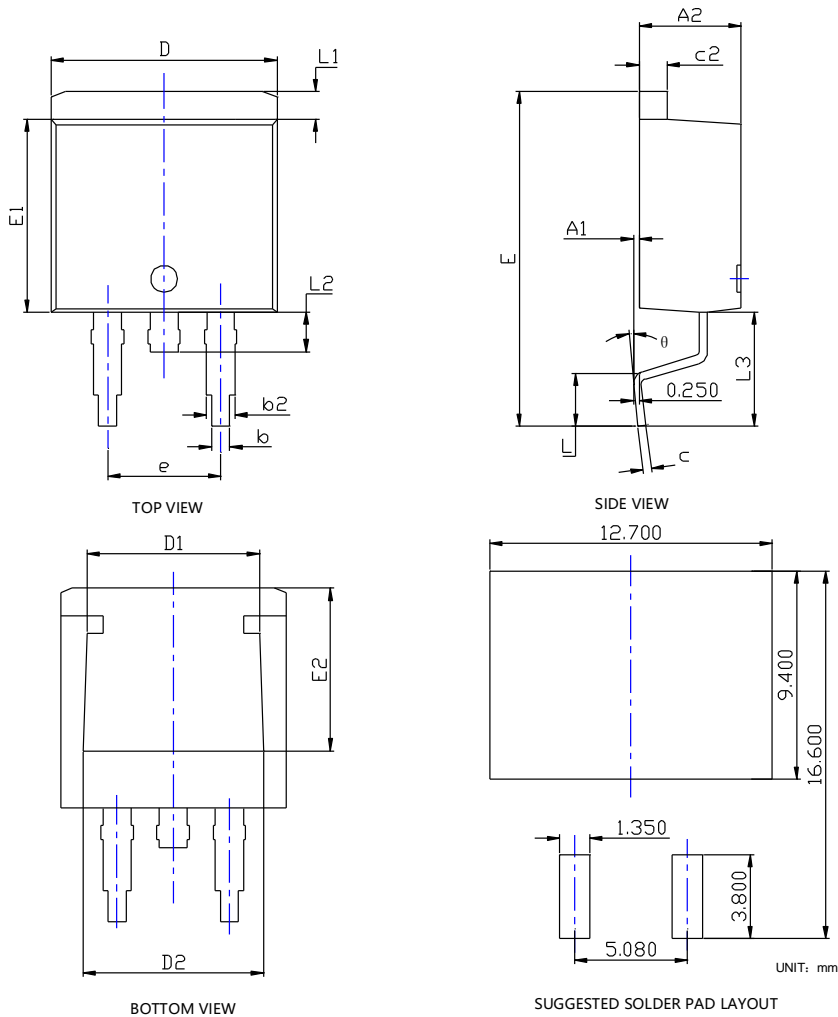


Figure14. Safe Operation Area



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TO-263-HY Package information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.340
D	0.394	0.400	0.406	10.000	10.150	10.300
D1	0.295	0.307	0.319	7.500	7.800	8.100
D2	0.303	0.315	0.327	7.700	8.000	8.300
E	0.571	0.591	0.610	14.500	15.000	15.500
E1	0.337	0.341	0.348	8.550	8.700	8.850
E2	0.276	0.287	0.299	7.000	7.300	7.600
e	0.200BSC			5.080BSC		
L	0.070	---	0.110	1.790	---	2.790
L1	0.044	---	0.056	1.120	---	1.420
L2	0.030	---	0.070	0.770	---	1.770
L3	0.197REF			5.000REF		
θ	0°	---	8°	0°	---	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



YJB155G04H

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